

## Advance Information

### Description

The μPD4216402 and the μPD4217402 are static-column dynamic RAMs organized as 4,194,304 words by 4 bits and designed to operate from a single +5-volt power supply. Advanced polycide technology minimizes silicon area and provides high storage cell capacity, high performance, and high reliability. A single-transistor dynamic storage cell and advanced CMOS circuitry throughout ensure minimum power dissipation, while an on-chip circuit internally generates the negative-voltage substrate bias—automatically and transparently.

The three-state I/O pins are controlled by  $\overline{CS}$  independent of  $\overline{RAS}$ . After a valid read or read-modify-write cycle, data is held on the outputs by maintaining  $\overline{CS}$  low. Data outputs return to high impedance when  $\overline{CS}$  goes high. Static-column read and write cycles can be executed by cycling  $\overline{CS}$ .

Refreshing may be accomplished by a  $\overline{CS}$  before  $\overline{RAS}$  cycle that internally generates the refresh address. Refreshing can also be accomplished by  $\overline{RAS}$ -only refresh cycles or by normal read or write cycles.

Two versions of the 4,194,304 by 4-bit static-column dynamic RAM are available. The μPD4216402 version uses 4096 address combinations of  $A_0 - A_{11}$  to refresh the memory during a 64-ms refresh period. The μPD4217402 version uses 2048 address combinations of  $A_0 - A_{10}$  to refresh the memory during a 32-ms refresh period.

To access the memory during read, write, and read-modify-write cycles, the μPD4216402 uses row address combinations of  $A_0 - A_{11}$  and column address combinations of  $A_0 - A_9$ . The μPD4217402 uses row and column address combinations of  $A_0 - A_{10}$ .

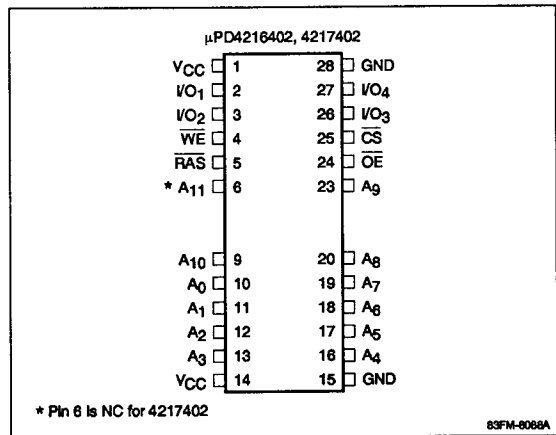
### Features

- 4,194,304 by 4-bit organization
- Single +5-volt power supply
- Static-column option
- Low power dissipation
- $\overline{CS}$  before  $\overline{RAS}$  refresh cycles
- Multiplexed address inputs

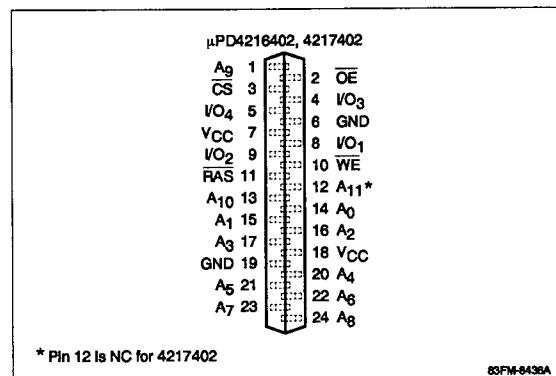
- On-chip substrate bias generator
- TTL-compatible inputs and outputs
- Nonlatched, three-state outputs
- Low input capacitance
- 4096 refresh cycles every 64 ms (4216402); 2048 refresh cycles every 32 ms (4217402)
- 28/24-pin SOJ (400-mil), 24-pin ZIP (475-mil), and 28/24-pin TSOP plastic packaging

### Pin Configurations

#### 28/24-Pin Plastic SOJ



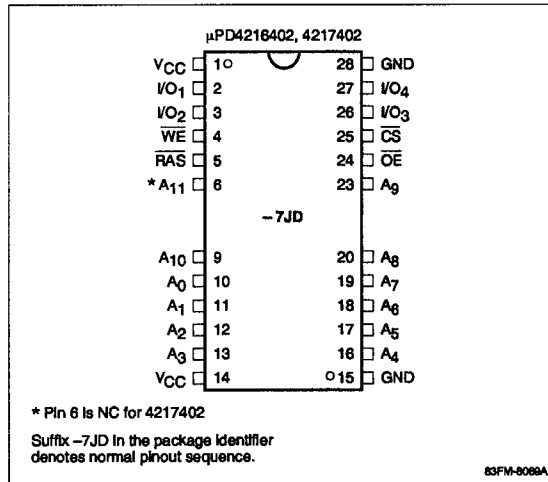
#### 24-Pin Plastic ZIP



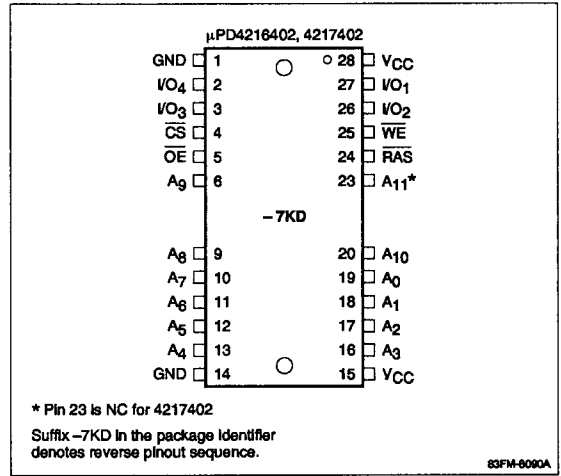
## μPD4216402, 4217402

### Pin Configurations (cont)

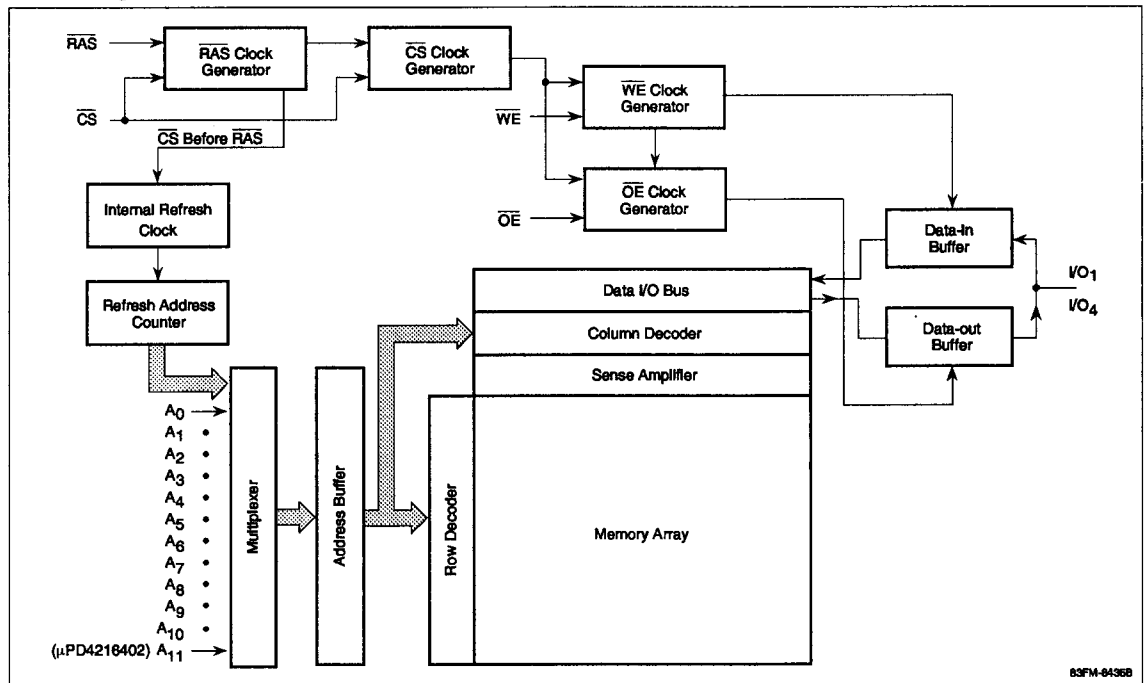
#### 28/24-Pin Plastic TSOP (Normal Pinouts)



#### 28/24-Pin Plastic TSOP (Reverse Pinouts)



### Block Diagram



### Ordering Information, μPD4216402

Part Number	RAS Access Time (max)	R/W Cycle Time (max)	Fast-Page Cycle (max)	Number of Refresh Cycles	Package
μPD4216402LE-60	60 ns	110 ns	40 ns	4096	28/24-pin plastic SOJ (400 mil)
LE-70	70 ns	130 ns	45 ns		
LE-80	80 ns	150 ns	50 ns		
LE-10	100 ns	180 ns	60 ns		
μPD4216402V-60	60 ns	110 ns	40 ns	4096	24-pin plastic ZIP
V-70	70 ns	130 ns	45 ns		
V-80	80 ns	150 ns	50 ns		
V-10	100 ns	180 ns	60 ns		
μPD4216402G5-60	60 ns	110 ns	40 ns	4096	28/24-pin plastic TSOP (normal pinouts)
G5-70	70 ns	130 ns	45 ns		
G5-80	80 ns	150 ns	50 ns		
μPD4216402G5M-60	60 ns	110 ns	40 ns	4096	28/24-pin plastic TSOP (reverse pinouts)
G5M-70	70 ns	130 ns	45 ns		
G5M-80	80 ns	150 ns	50 ns		

### Ordering Information, μPD4217402

Part Number	RAS Access Time (max)	R/W Cycle Time (max)	Fast-Page Cycle (max)	Number of Refresh Cycles	Package
μPD4217402LE-60	60 ns	110 ns	40 ns	2048	28/24-pin plastic SOJ (400 mil)
LE-70	70 ns	130 ns	45 ns		
LE-80	80 ns	150 ns	50 ns		
LE-10	100 ns	180 ns	60 ns		
μPD4217402V-60	60 ns	110 ns	40 ns	2048	24-pin plastic ZIP
V-70	70 ns	130 ns	45 ns		
V-80	80 ns	150 ns	50 ns		
V-10	100 ns	180 ns	60 ns		
μPD4217402G5-60	60 ns	110 ns	40 ns	2048	28/24-pin plastic TSOP (normal pinouts)
G5-70	70 ns	130 ns	45 ns		
G5-80	80 ns	150 ns	50 ns		
μPD4217402G5M-60	60 ns	110 ns	40 ns	2048	28/24-pin plastic TSOP (reverse pinouts)
G5M-70	70 ns	130 ns	45 ns		
G5M-80	80 ns	150 ns	50 ns		